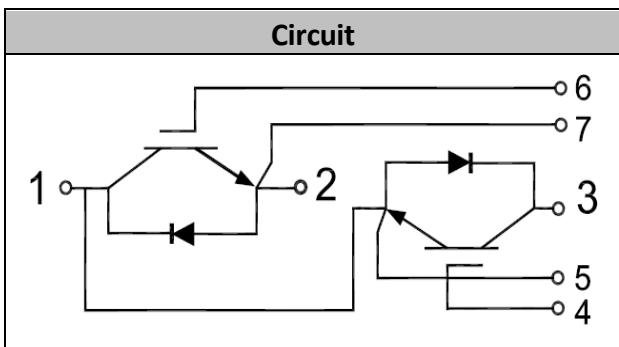


## IGBT Modules

$V_{CES}$	1200V
$I_c$	150A

## Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)
- Soft switching welding machine



## Features

- Low  $V_{CE(sat)}$  with Trench technology
- $V_{ce(sat)}$  with positive temperature coefficient
- High short circuit capability(10us)
- Including ultra fast & soft recovery anti-parallel FWD
- Low inductance
- Maximum junction temperature 175°C

## ● IGBT

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_c=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_c$	$T_c=100^{\circ}C$	150	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	300	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_c=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	833	W



## Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=4mA, T_{vj}=25^{\circ}C$	5.2	5.9	6.4	V
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=150A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.85		V
		$I_C=150A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.05		
Gate Charge	$Q_G$			1.56		uC
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		11.0		nF
Reverse Transfer Capacitance	$C_{res}$			0.5		nF
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=150A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=4.7\Omega$ $T_{vj}=25^{\circ}C$		196		ns
Rise Time	$t_r$			57		ns
Turn-off Delay Time	$t_{d(off)}$			263		ns
Fall Time	$t_f$			126		ns
Energy Dissipation During Turn-on Time	$E_{on}$			18		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			7.9		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=150A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=4.7\Omega$ $T_{vj}=150^{\circ}C$		202		ns
Rise Time	$t_r$			69		ns
Turn-off Delay Time	$t_{d(off)}$			304		ns
Fall Time	$t_f$			191		ns
Energy Dissipation During Turn-on Time	$E_{on}$			24.6		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			10.6		mJ
SC Data	$I_{sc}$	$t_p \leq 10\mu s, V_{GE}=15V,$ $T_{vj}=150^{\circ}C, V_{CC}=900V,$ $V_{CEM} \leq 1200V$		890		A



## ● Diode

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	$I_F$		150	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1\text{ms}$	300	A

### Characteristic Values

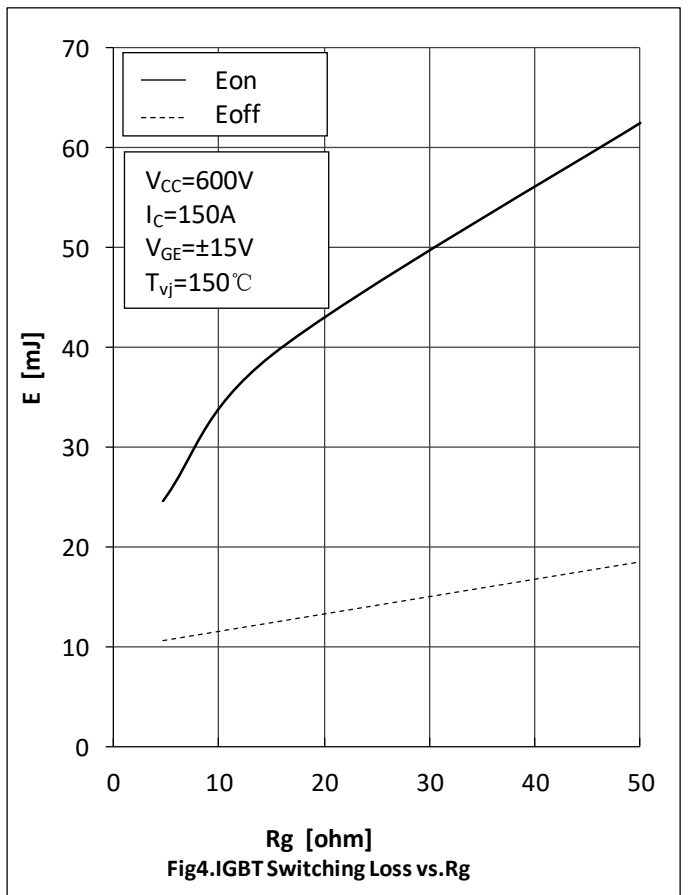
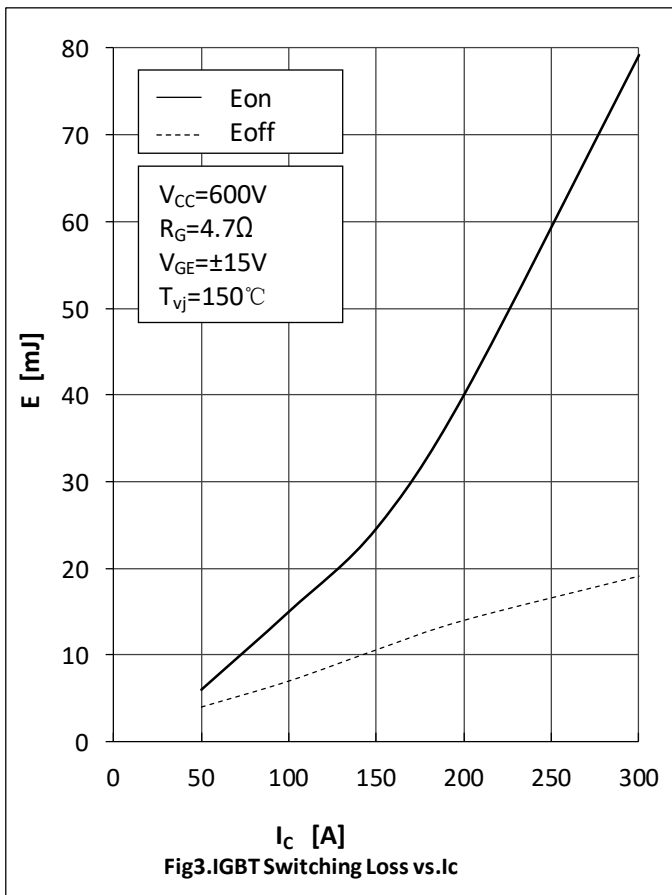
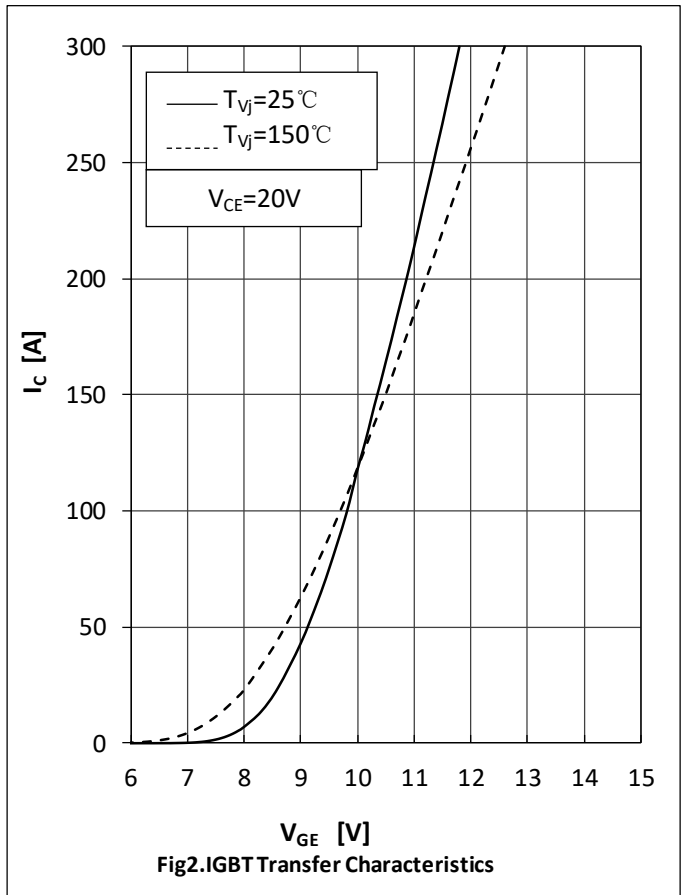
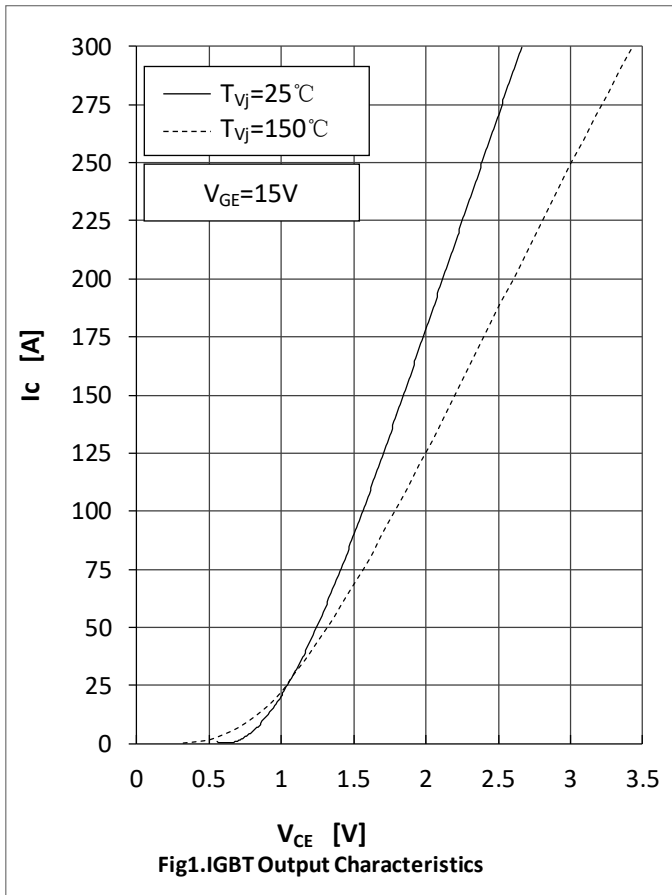
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	$V_F$	$I_F=150\text{A}, T_{vj}=25^{\circ}\text{C}$		1.90	2.40	V
		$I_F=150\text{A}, T_{vj}=125^{\circ}\text{C}$		1.75		
Recovered Charge	$Q_{rr}$	$I_F=150\text{A}$		8.6		$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600\text{V}$ $-di_F/dt = 2000\text{A}/\mu\text{s}$		48		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=25^{\circ}\text{C}$		2.7		mJ
Recovered Charge	$Q_{rr}$	$I_F=150\text{A}$		23.4		$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rr}$	$V_R=600\text{V}$ $-di_F/dt = 2000\text{A}/\mu\text{s}$		70		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj}=150^{\circ}\text{C}$		8.2		mJ

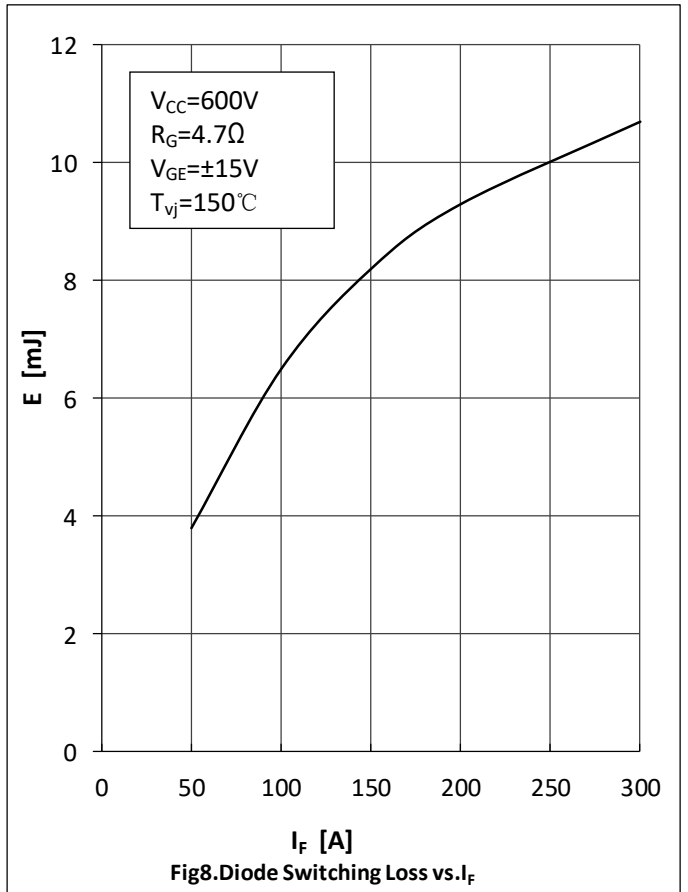
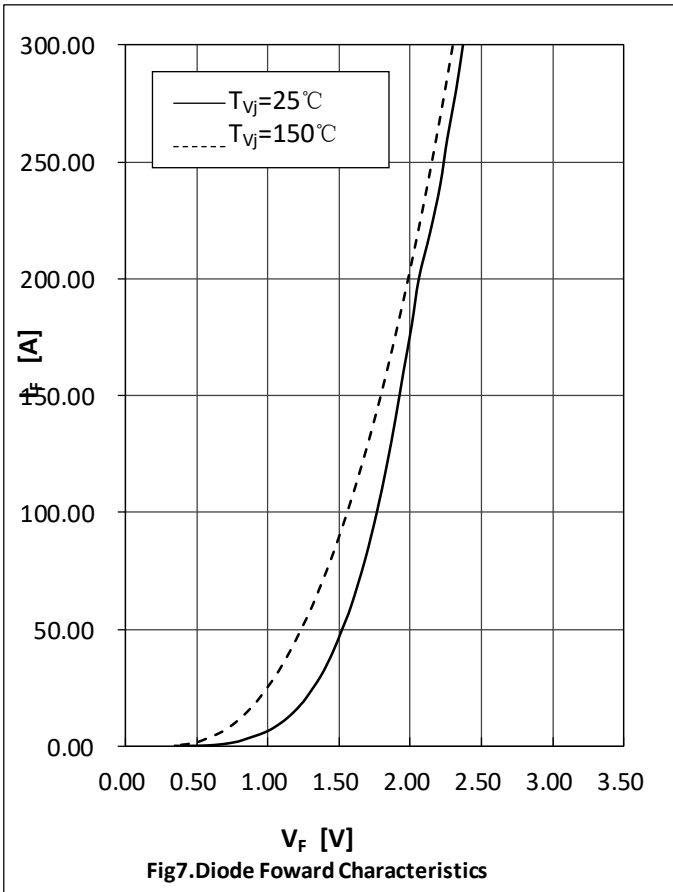
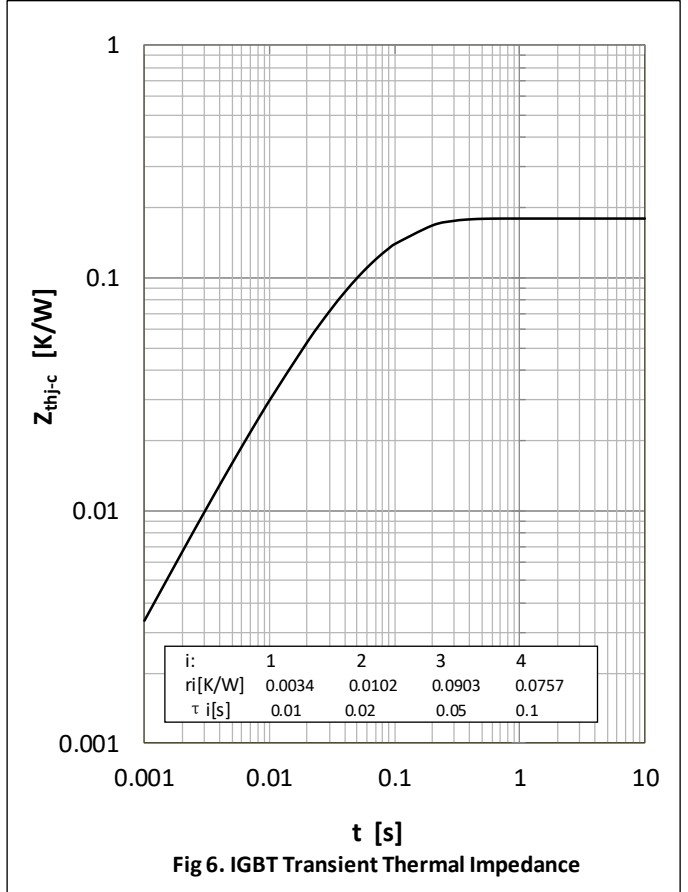
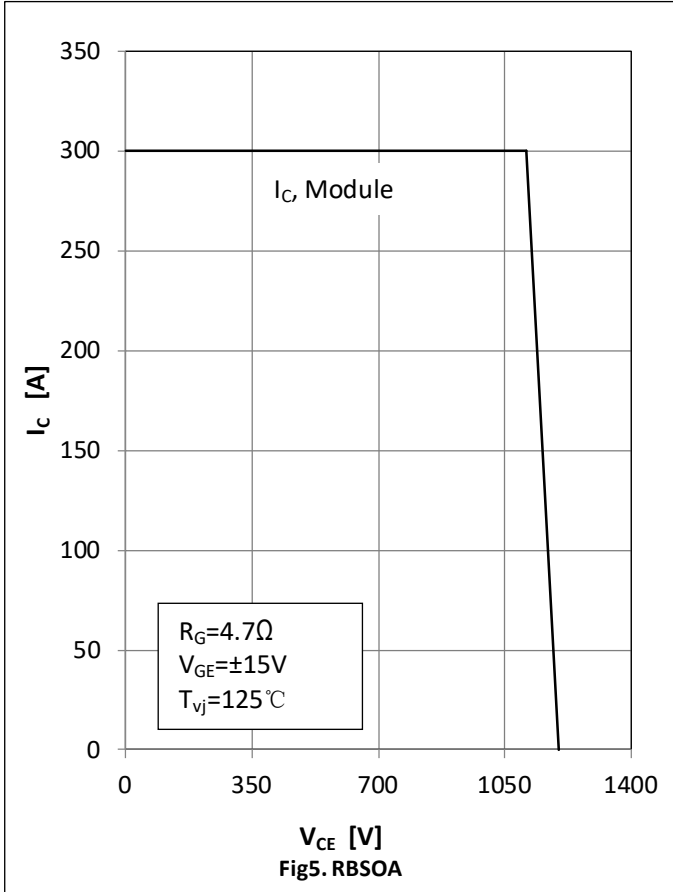


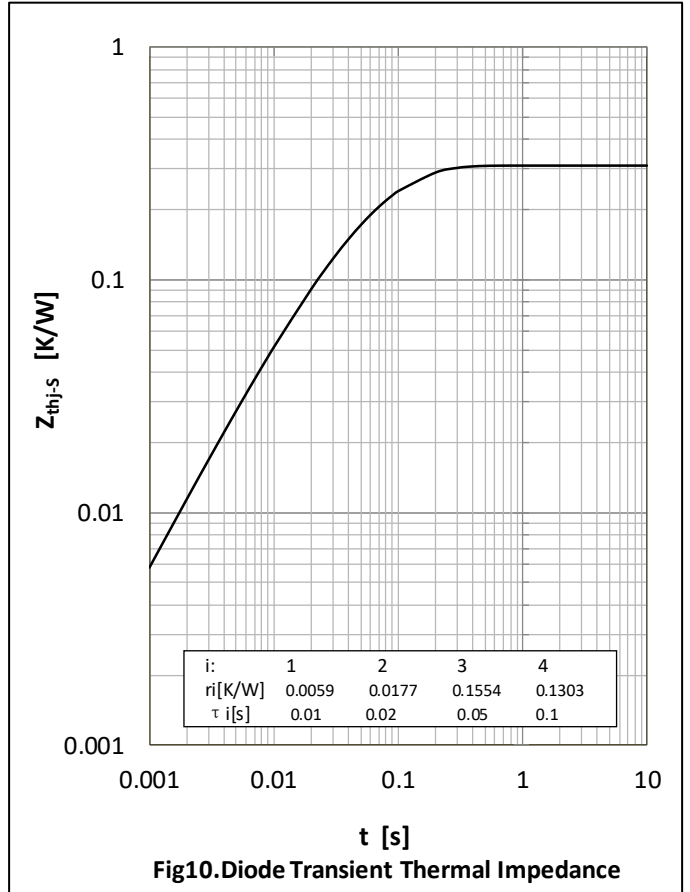
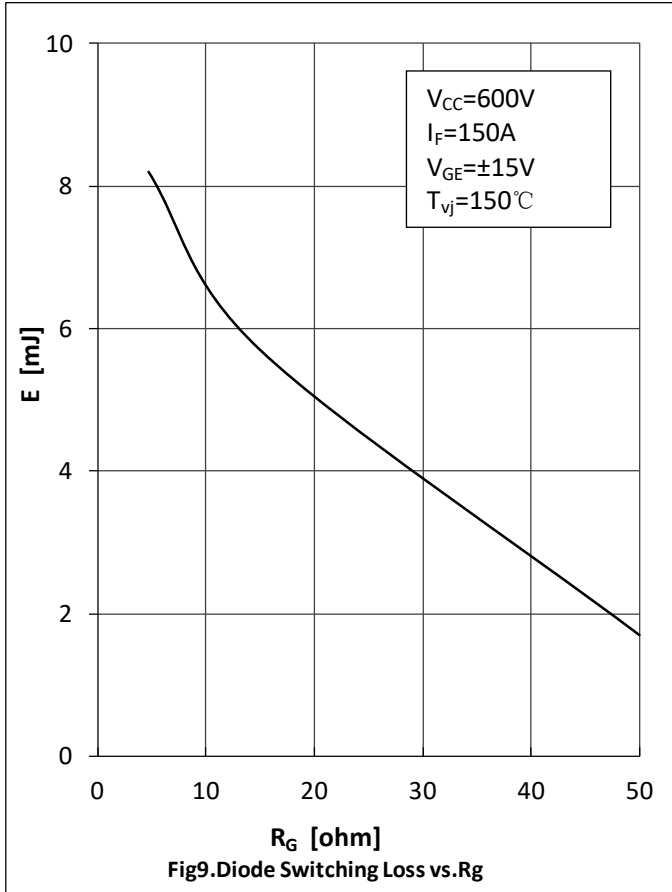
## ● Module Characteristics

$T_c=25^{\circ}\text{C}$  unless otherwise specified

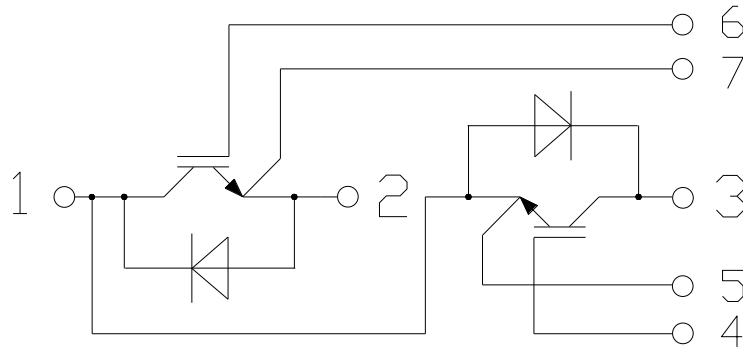
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	$V_{\text{isol}}$	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{\text{jmax}}$				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$		-40		125	$^{\circ}\text{C}$
Thermal Resistance Junction-to Case	$R_{\text{eJC}}$	per IGBT			0.18	K/W
		per Diode			0.31	
Thermal Resistance Case-to Sink	$R_{\text{eCS}}$	Conductive grease applied		0.035		K/W
Module Electrodes Torque	$M_t$	Recommended(M6)	3.0		5.0	N·m
Module-to-Sink Torque	$M_s$	Recommended(M6)	3.0		5.0	N·m
Weight of Module	G			315		g





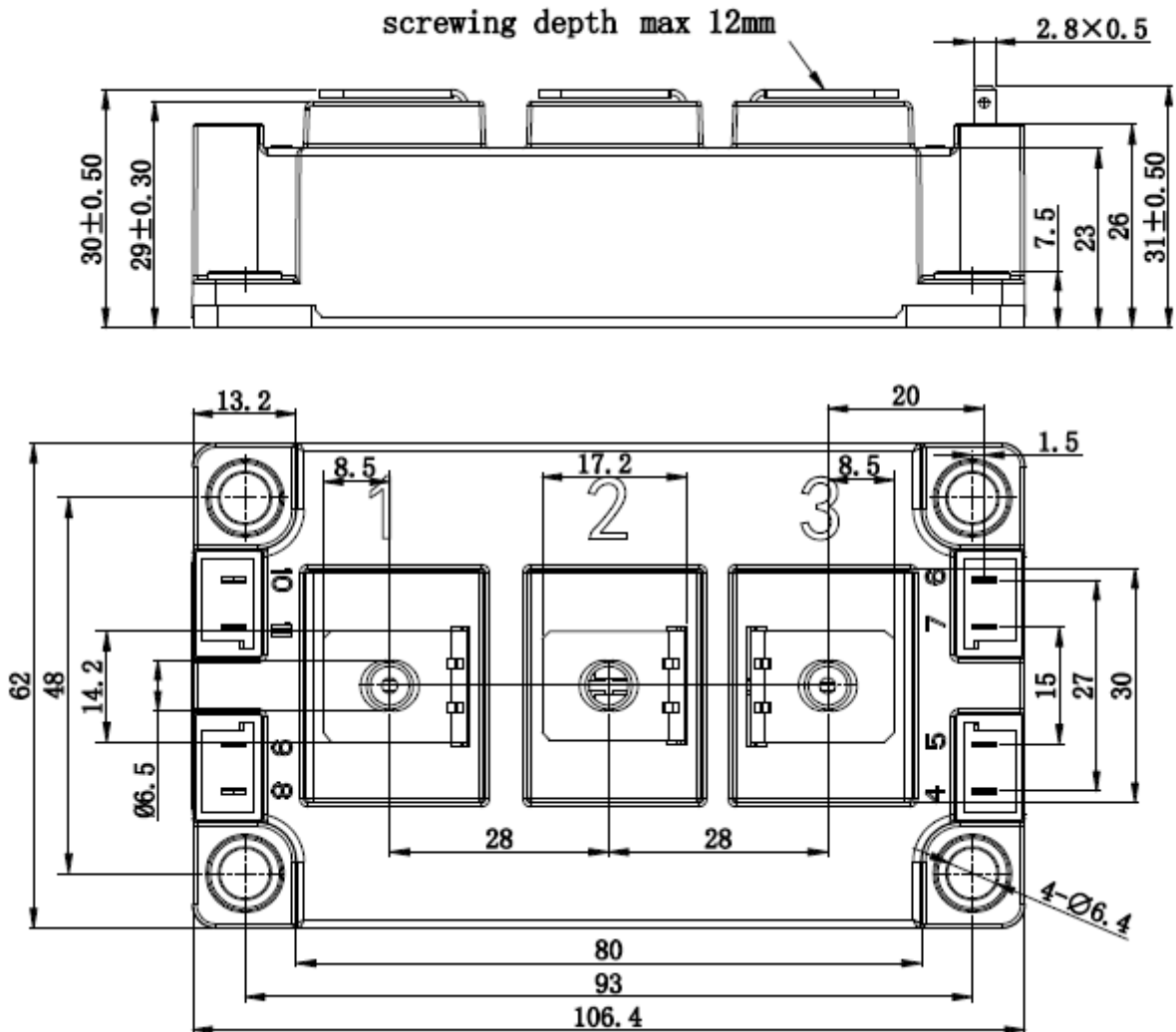


● **Circuit Diagram**



● **Package Outline Information**

**Dimensions in Millimeters**







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